

Low Threshold 2.5 Gbps 850 nm VCSEL

Part Number: VG2B-7010

Applications: 2.125 / 2.5

Absolute Maximum Ratings (T = 25°C):

Parameter	Symbol	Unit	Min.		Max.	Test Condition	Note
Forward Current	$I_{\max}$	mA			10		
Reverse Voltage	V_r	V			5		
Operating Temperature	T_{op}	°C	0		85		
Storage Temperature	T_{stg}	°C	- 40		100		
Maximum Die Exposure	$T_{\max}$	°C			260	For 10 seconds	

Electro-optical Characteristics (T = 25°C, unless noted otherwise):

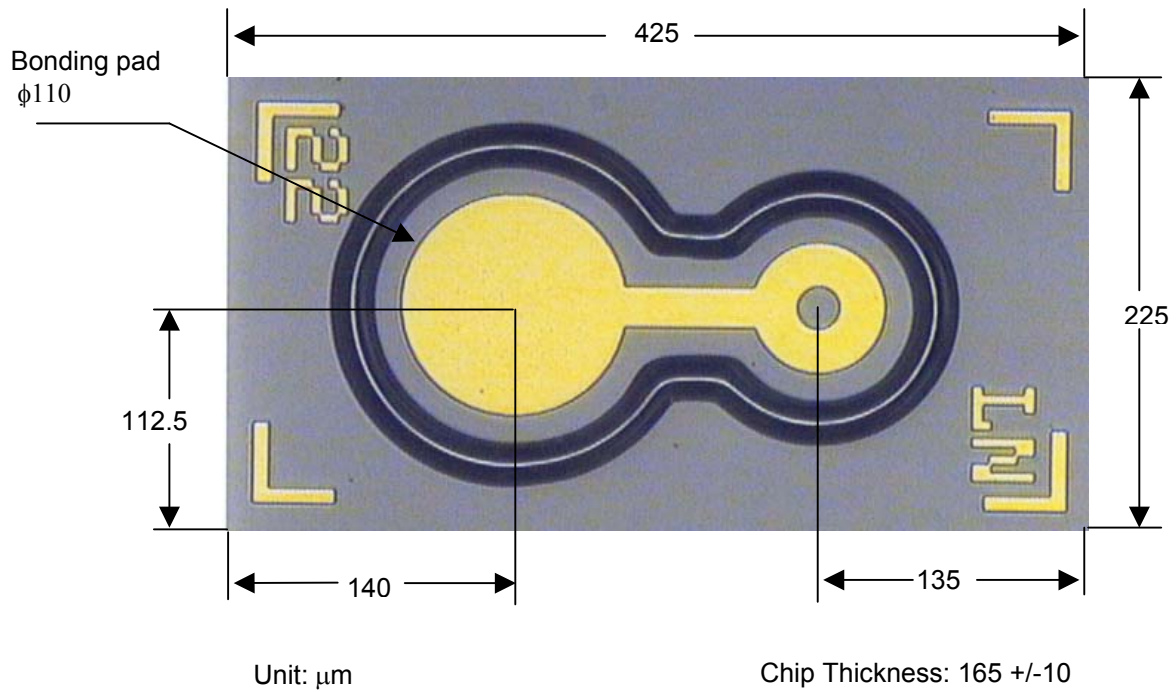
Parameter	Symbol	Unit	Min.	Typ.	Max.	Test Condition	Note
Threshold Current	I_{th}	mA		1.5	2.5		
Ith Temperature Variation	ΔI_{th}	mA	-1.5		1.5	25°C to 95°C	
Forward Voltage	V_f	V		2.0	2.2	@ 10 mA	
Differential Resistance	R_s	Ω		35	50	@ 10 mA	
Reverse Voltage	V_r	V	5			@ -10 μ A	
Slope Efficiency	η	mW/mA	0.2	0.3	0.5	@ 10 mA	
Optical Power	P_o	mW	1.5	2.0		@ 8 mA	
Slope Efficiency temp-coeff.	$\Delta\eta/\Delta T$	%/°C	-0.6			25-90°C @ 10 mA	
Peak Wavelength	λ	nm	830	845	860	@ 2 mW	
Beam Divergence	θ	deg			30	Full width, $1/e^2$	
Rise Time	τ_r	ps		90		20-80% $I_{\text{bias}} = 11\text{mA}$	
Fall Time	τ_f	ps		100		20-80% $I_{\text{bias}} = 11\text{mA}$	

Chip configuration:

1. Top contact: Anode; Bottom contact: Cathode.
2. Dimension: 225 μ m (Wide) x 425 μ m (Long) x 165 μ m (Thick)

* Specifications are subject to change without notice.
* Screening per customer-specified reject limits is available.

December, 2001



VCSEL Chip Top View